

	Hits	Search Text	DBs
1	272	((substrate or wafer or surface or interlayer or device or plate) same (low\$3k or dielectric or silicon\$5nitride or SiON) same ((upper\$3 near5 portion) or sacrific\$4 or cap\$2 or SiO\$2 or (silicon near5 \$3oxide)) same (convert\$4 or (plasma\$4 near9 (ash\$5 or treat\$6 or oxidation or oxidi\$5)))) and ((pattern\$6 or photolithograph\$8 or lithograph\$6) same (via or trench or dual\$9damascene)) and ((photoresist or resist or photosensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same develop\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
3	107	((substrate or wafer or surface or interlayer or device or plate) same (low\$3k or dielectric or silicon\$5nitride or SiON) same ((upper\$3 near5 portion) or sacrific\$4 or cap\$2 or SiO\$2 or (silicon near5 \$3oxide)) same (convert\$4 or (plasma\$4 near9 (ash\$5 or treat\$6 or oxidation or oxidi\$5)))) and ((pattern\$6 or photolithograph\$8 or lithograph\$6) same (via or trench or dual\$9damascene)) and ((photoresist or resist or photosensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same develop\$4 same (oxide or protective or barrier or etch\$4stop))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
4	68	((substrate or wafer or surface or interlayer or device or plate) same (low\$3k or dielectric or silicon\$5nitride or SiON) same ((upper\$3 near5 portion) or sacrific\$4 or cap\$2 or SiO\$2 or (silicon near5 \$3oxide)) same (convert\$4 or (plasma\$4 near9 (ash\$5 or treat\$6 or oxidation or oxidi\$5)))) and ((pattern\$6 or photolithograph\$8 or lithograph\$6) same (via or trench or dual\$9damascene)) and ((photoresist or resist or photosensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same develop\$4 same (oxide or protective or barrier or etch\$4stop)) and via and trench\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	16	((substrate or wafer or surface or interlayer or device or plate) same (low\$3k or dielectric or silicon\$5nitride or SiON or (low\$3 near9 dielectric)) same (heat\$4 or bak\$4 or thermal) same ((upper\$3 near5 portion) or (sacrific\$4 near11 oxide) or cap\$2 or SiO\$2 or (silicon near5 \$3oxide)) same (convert\$4 or (plasma\$4 near9 (ash\$5 or treat\$6 or oxidation or oxidi\$5)) or plasma or CVD or PECVD)) and ((pattern\$6 or photolithograph\$8 or lithograph\$6) same (via or trench or dual\$9damascene)) and ((photoresist or resist or photosensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same develop\$4) and (pattern\$4 same (oxide or protective or barrier or (sacrificial near9 oxide))) and ((out\$5gas\$5 or dissipat\$4 or eliminat\$4) same (volatile or contaminat\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
6	41	((low\$3k or dielectric or silicon\$5nitride or SiON or (low\$4 near16 dielectric)) same ((upper\$3 near5 portion) or sacrific\$4 or cap\$2 or SiO\$2 or (silicon near5 \$3oxide)) same (convert\$4 or (plasma\$4 near9 (ash\$5 or treat\$6 or oxidation or oxidi\$5)))) and ((low\$3k or dielectric or silicon\$5nitride or SiON or (low\$4 near16 dielectric)) same (heat\$9 or bak\$4 or anneal\$4)) and ((pattern\$6 or photolithograph\$8 or lithograph\$6) same (via or trench or dual\$9damascene)) and via and trench and ((out\$5gas\$5 or dissipat\$4 or eliminat\$4 or rid\$4 or dispos\$4 or exhaust\$4) same (volatile or contaminat\$4 or poison\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	38	S6 NOT S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB